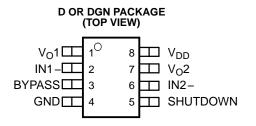




#### 150-mW STEREO AUDIO POWER AMPLIFIER

#### **FEATURES**

- 150-mW Stereo Output
- PC Power Supply Compatible
  - Fully Specified for 3.3-V and 5-V Operation
  - Operation to 2.5 V
- Pop Reduction Circuitry
- Internal Midrail Generation
- Thermal and Short-Circuit Protection
- Surface-Mount Packaging
  - PowerPAD™ MSOP
  - SOIC
- Pin Compatible With LM4880 and LM4881 (SOIC)

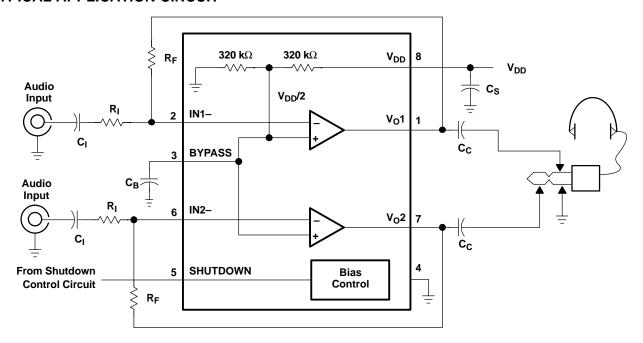


#### **DESCRIPTION**

The TPA122 is a stereo audio power amplifier packaged in either an 8-pin SOIC, or an 8-pin PowerPAD<sup>TM</sup> MSOP package capable of delivering 150 mW of continuous RMS power per channel into 8- $\Omega$  loads. Amplifier gain is externally configured by means of two resistors per input channel and does not require external compensation for settings of 1 to 10.

THD+N when driving an 8- $\Omega$  load from 5 V is 0.1% at 1 kHz, and less than 2% across the audio band of 20 Hz to 20 kHz. For 32- $\Omega$  loads, the THD+N is reduced to less than 0.06% at 1 kHz, and is less than 1% across the audio band of 20 Hz to 20 kHz. For 10-k $\Omega$  loads, the THD+N performance is 0.01% at 1 kHz, and less than 0.02% across the audio band of 20 Hz to 20 kHz.

#### TYPICAL APPLICATION CIRCUIT



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **AVAILABLE OPTIONS**

	PACKAGED DEVIC	MSOP	
T <sub>A</sub>	SMALL OUTLINE <sup>(1)</sup> (D)	MSOP <sup>(1)</sup> (DGN)	SYMBOLIZATION
-40°C to 85°C	TPA122D	TPA122DGN	TI AAE

(1) The D and DGN packages are available in left-ended tape and reel only (e.g., TPA122DR, TPA122DGNR).

#### **Terminal Functions**

TERMINA	AL	1/0	DESCRIPTION	
NAME	NO.	"	DESCRIPTION	
BYPASS	3	ı	Tap to voltage divider for internal mid-supply bias supply. Connect to a 0.1 $\mu$ F to 1 $\mu$ F low ESR capacitor for best performance.	
GND	4	ı	GND is the ground connection.	
IN1-	2	1	IN1- is the inverting input for channel 1.	
IN2-	6	ı	IN2- is the inverting input for channel 2.	
SHUTDOWN	5	- 1	Puts the device in a low quiescent current mode when held high	
$V_{DD}$	8	1	V <sub>DD</sub> is the supply voltage terminal.	
V <sub>O</sub> 1	1	0	V <sub>O</sub> 1 is the audio output for channel 1.	
V <sub>O</sub> 2	7	0	V <sub>O</sub> 2 is the audio output for channel 2.	

#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)(1)

		UNIT
$V_{DD}$	Supply voltage	6 V
VI	Input voltage	–0.3 V to V <sub>DD</sub> + 0.3 V
	Continuous total power dissipation	Internally limited
TJ	Operating junction temperature range	-40°C to 150°C
T <sub>stg</sub>	Storage temperature range	−65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW
DGN	2.14 W <sup>(1)</sup>	17.1 mW/°C	1.37 W	1.11 W

(1) See the Texas Instruments document, PowerPAD Thermally Enhanced Package Application Report (SLMA002), for more information on the PowerPAD package. The thermal data was measured on a PCB layout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD of that document.



#### **RECOMMENDED OPERATING CONDITIONS**

		MIN	MAX	UNIT
$V_{DD}$	Supply voltage	2.5	5.5	V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C
V <sub>IH</sub>	High-level input voltage, (SHUTDOWN)	$0.80 \times V_{DD}$		V
V <sub>IL</sub>	Low-level input voltage, (SHUTDOWN)		$0.40 \times V_{DD}$	V

#### DC ELECTRICAL CHARACTERISTICS

at  $T_A = 25$ °C,  $V_{DD} = 3.3$  V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>oo</sub>	Output offset voltage				10	mV
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 3.2 V to 3.4 V		83		dB
I <sub>DD</sub>	Supply current	V <sub>DD</sub> = 2.5, SHUTDOWN = 0 V		1.5	3	mA
I <sub>DD(SD)</sub>	Supply current in SHUTDOWN mode	V <sub>DD</sub> = 2.5, SHUTDOWN = V <sub>DD</sub>		10	50	μA
Z <sub>I</sub>	Input impedance			> 1		ΜΩ

#### **AC OPERATING CHARACTERISTICS**

 $V_{DD}$  = 3.3 V,  $T_A$  = 25°C,  $R_L$  = 8  $\Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP N	MAX UNIT
Po	Output power (each channel)	THD≤ 0.1%	70 <sup>(1)</sup>	mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 70 mW, 20 Hz–20 kHz	2%	
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 5%	> 20	kHz
	Phase margin	Open loop	58°	
	Supply ripple rejection	f = 1 kHz	68	dB
	Channel/channel output separation	f = 1 kHz	86	dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 100 mW	100	dB
V <sub>n</sub>	Noise output voltage		9.5	μV(rms)

<sup>(1)</sup> Measured at 1 kHz

#### DC ELECTRICAL CHARACTERISTICS

at  $T_A = 25$ °C,  $V_{DD} = 5.5$  V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Voo	Output offset voltage				10	mV
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 4.9 V to 5.1 V		76		dB
I <sub>DD</sub>	Supply current	SHUTDOWN = 0 V		1.5	3	mA
I <sub>DD(SD)</sub>	Supply current in SHUTDOWN mode	SHUTDOWN = V <sub>DD</sub>		60	100	μΑ
I <sub>IH</sub>	High-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_{I} = V_{DD}$			1	μΑ
$ I_{IL} $	Low-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_{I} = 0 \text{ V}$			1	μΑ
Z <sub>I</sub>	Input impedance			> 1		$M\Omega$



#### **AC OPERATING CHARACTERISTICS**

 $V_{DD} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, R_L = 8 \Omega$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%		70(1)		mW
THD+N	Total harmonic distortion + noise	$P_{O} = 150 \text{ mW}, 20 \text{ Hz}-20 \text{ kHz}$		2%		
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 5%		> 20		kHz
	Phase margin	Open loop		56°		
	Supply ripple rejection ratio	f = 1 kHz		68		dB
	Channel/channel output separation	f = 1 kHz		86		dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 150 mW		100		dB
V <sub>n</sub>	Noise output voltage			9.5		μV(rms)

<sup>(1)</sup> Measured at 1 kHz

#### **AC OPERATING CHARACTERISTICS**

 $V_{DD} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}, R_L = 32 \Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%	40(1)		mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 30 mW, 20 Hz–20 kHz	0.5%		
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 2%	> 20		kHz
	Phase margin	Open loop	58°		
	Supply ripple rejection	f = 1 kHz	68		dB
	Channel/channel output separation	f = 1 kHz	86		dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 100 mW	100		dB
V <sub>n</sub>	Noise output voltage		9.5		μV(rms)

<sup>(1)</sup> Measured at 1 kHz

#### **AC OPERATING CHARACTERISTICS**

 $\mathrm{V_{DD}} = 5~\mathrm{V},~\mathrm{T_A} = 25^{\circ}\mathrm{C},~\mathrm{R_L} = 32~\Omega$ 

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%	40 <sup>(1)</sup>		mW
THD+N	Total harmonic distortion + noise	P <sub>O</sub> = 60 mW, 20 Hz–20 kHz	0.4%		
B <sub>OM</sub>	Maximum output power BW	G = 10, THD < 2%	> 20		kHz
	Phase margin	Open loop	56°		
	Supply ripple rejection	f = 1 kHz	68		dB
	Channel/channel output separation	f = 1 kHz	86		dB
SNR	Signal-to-noise ratio	P <sub>O</sub> = 150 mW	100		dB
V <sub>n</sub>	Noise output voltage		9.5		μV(rms)

<sup>(1)</sup> Measured at 1 kHz

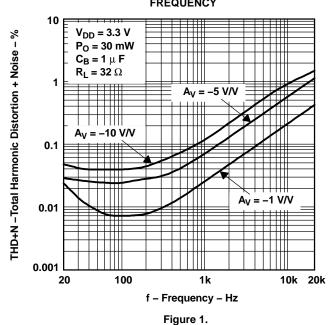


#### **TYPICAL CHARACTERISTICS**

#### **Table of Graphs**

			FIGURE
THD+N	Total harmonic distortion plus noise	vs Frequency	1, 2, 4, 5, 7, 8, 10, 11, 13, 14, 16, 17, 34, 36
		vs Output power	3, 6, 9, 12, 15, 18
	Supply ripple rejection	vs Frequency	19, 20
V <sub>n</sub>	Output noise voltage	vs Frequency	21, 22
	Crosstalk	vs Frequency	23-26, 37, 38
	Mute attenuation	vs Frequency	27, 28
	Open-loop gain and phase margin	vs Frequency	29, 30
	Output power	vs Load resistance	31, 32
	Phase	vs Frequency	39-44
I <sub>DD</sub>	Supply current	vs Supply voltage	33
SNR	Signal-to-noise ratio	vs Voltage gain	35
	Closed-loop gain	vs Frequency	39-44
	Power dissipation/amplifier	vs Output power	45, 46

# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

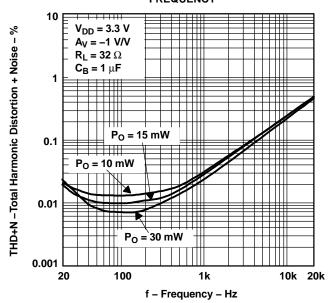
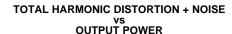
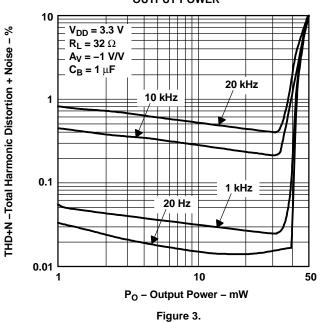


Figure 2.







### TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

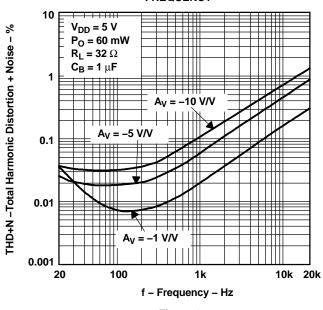
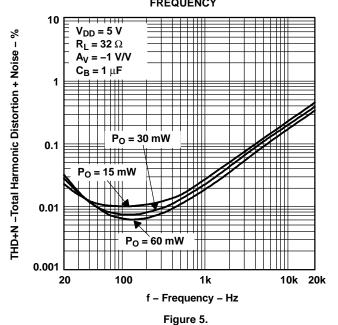


Figure 4.

### TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

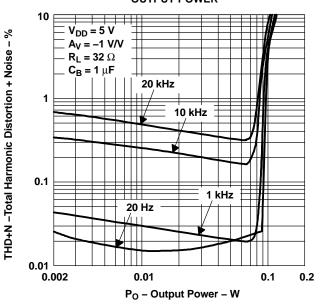
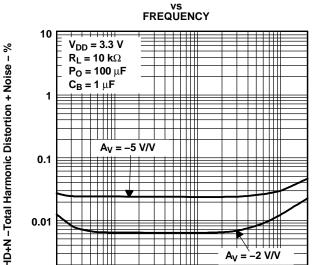


Figure 6.





**TOTAL HARMONIC DISTORTION + NOISE** 



# THD+N -Total Harmonic Distortion + Noise - % 0.001 20 100 10k 20k 1k f - Frequency - Hz

## **TOTAL HARMONIC DISTORTION + NOISE**

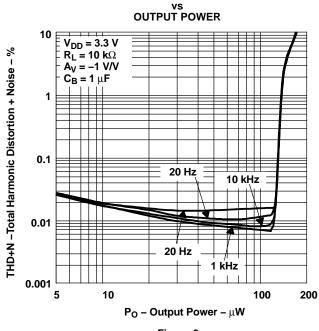


Figure 9.

### **TOTAL HARMONIC DISTORTION + NOISE** vs FREQUENCY

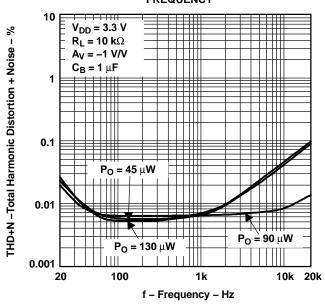


Figure 8.

### **TOTAL HARMONIC DISTORTION + NOISE** vs FREQUENCY

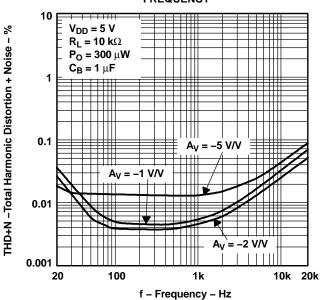


Figure 10.



# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

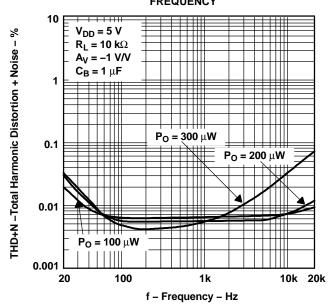


Figure 11.

# TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

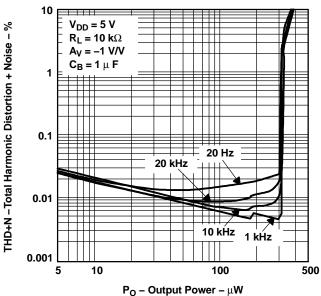


Figure 12.

# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

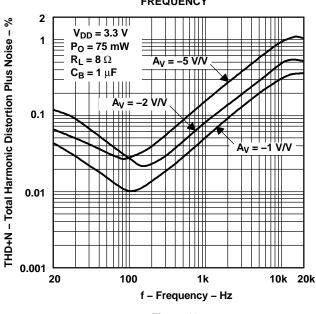


Figure 13.

# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

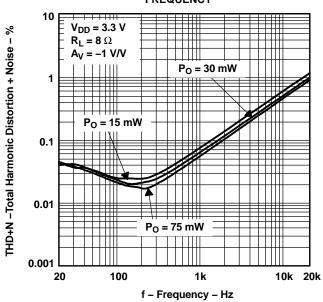
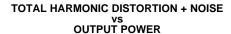
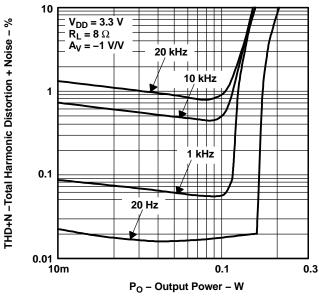


Figure 14.







## Figure 15.

# TOTAL HARMONIC DISTORTION + NOISE VS FREQUENCY

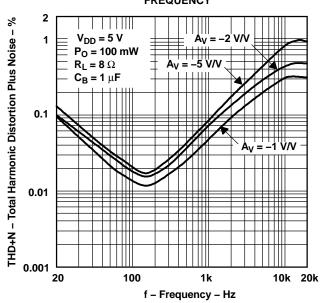


Figure 16.

# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

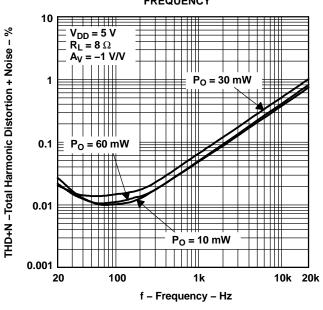


Figure 17.

### TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

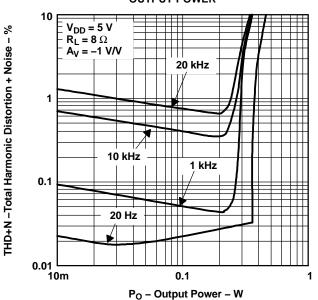


Figure 18.



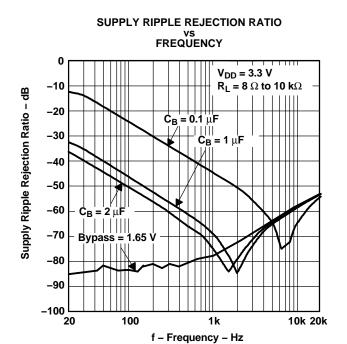
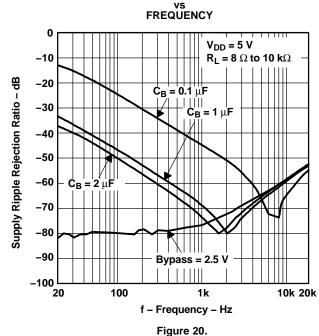
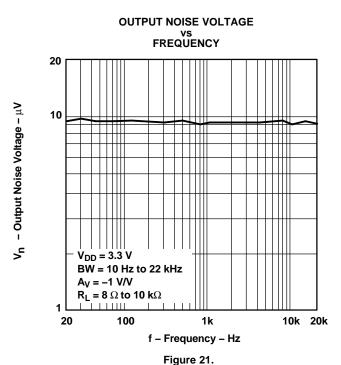
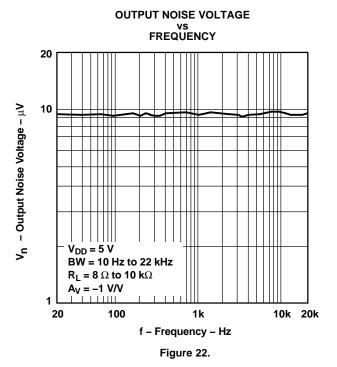


Figure 19.

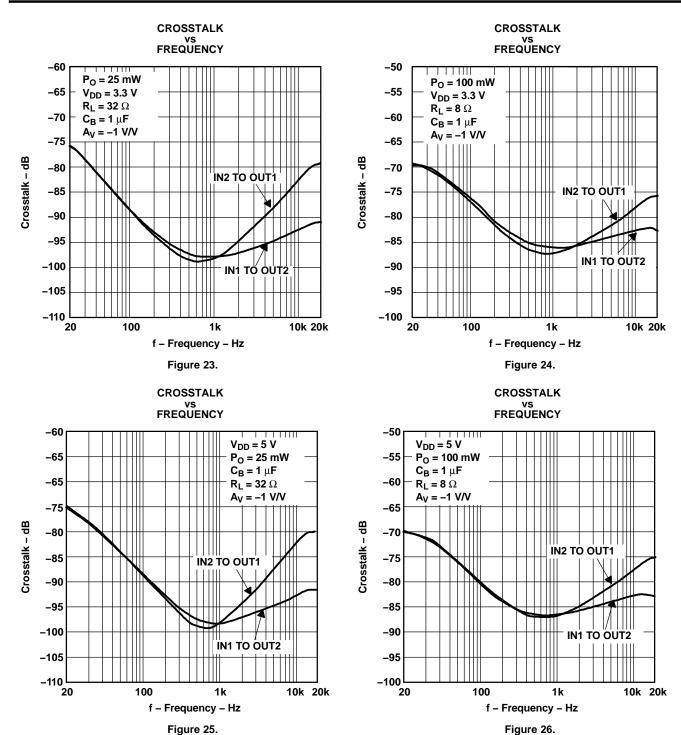


**SUPPLY RIPPLE REJECTION RATIO** 

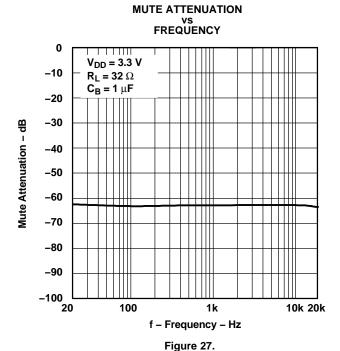












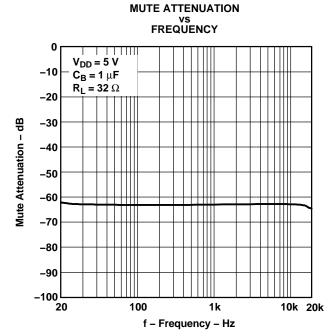
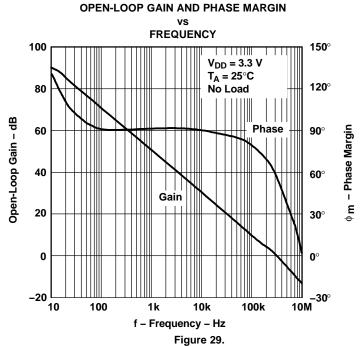


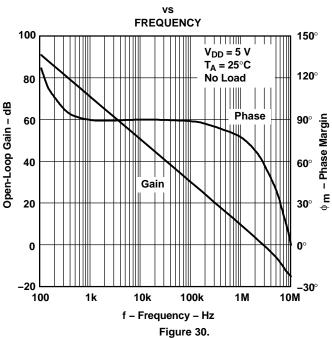
Figure 28.

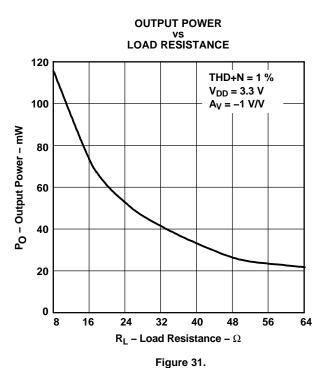
guie 27.

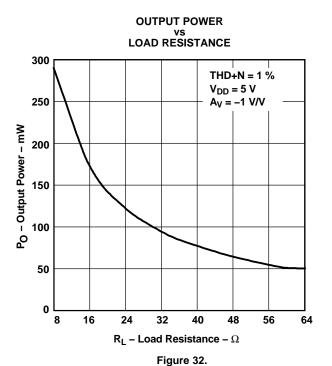




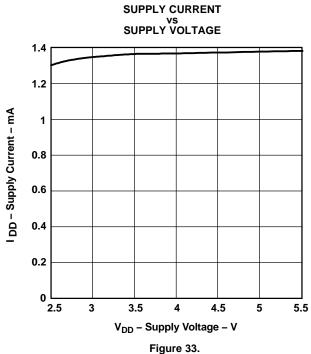
#### OPEN-LOOP GAIN AND PHASE MARGIN











# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

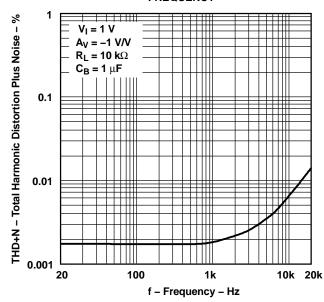
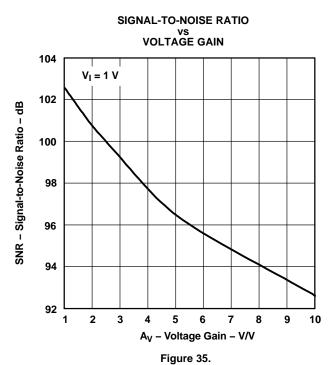
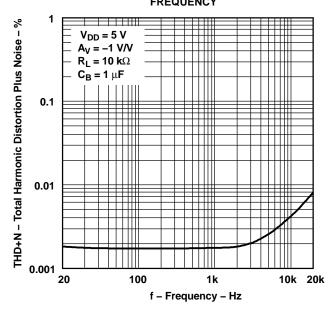


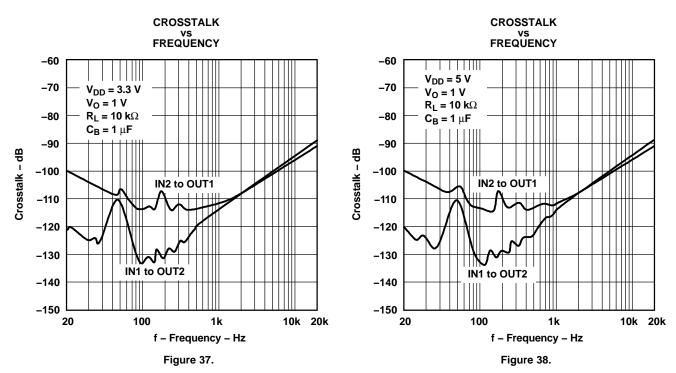
Figure 34.

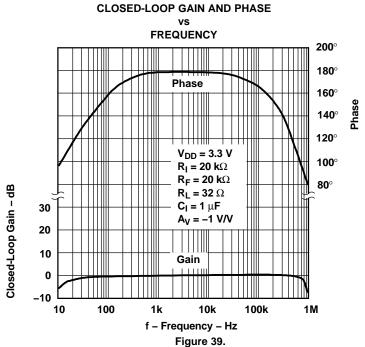


# TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



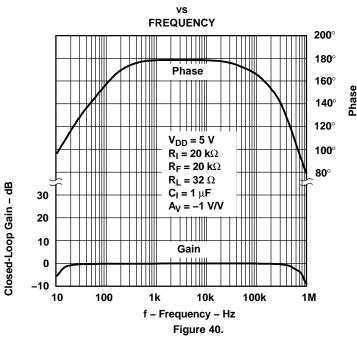




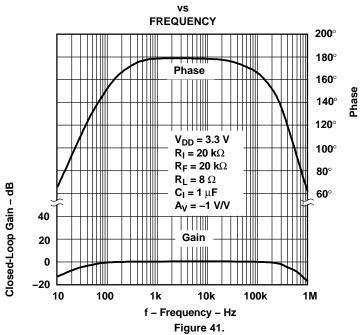




#### **CLOSED-LOOP GAIN AND PHASE**

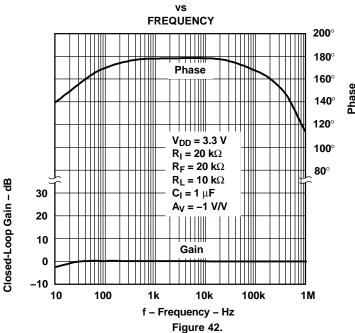


#### **CLOSED-LOOP GAIN AND PHASE**

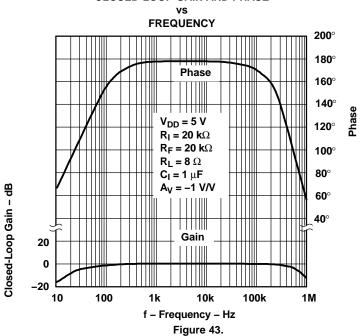






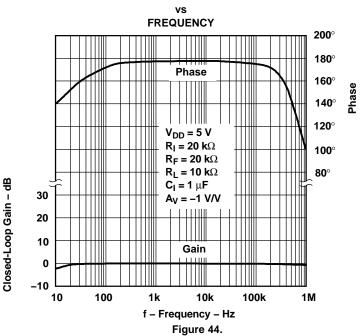


#### **CLOSED-LOOP GAIN AND PHASE**





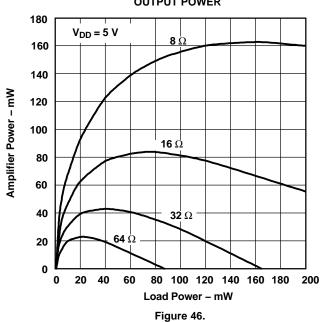
### CLOSED-LOOP GAIN AND PHASE



## POWER DISSIPATION/AMPLIFIER vs

#### vs OUTPUT POWER 80 $V_{DD} = 3.3 V$ 8 Ω 70 60 Amplifier Power - mW 50 40 16 Ω 30 $32^{\prime}\Omega$ 20 **64** Ω 10 20 40 80 100 120 140 160 180 0 60 200 Load Power - mW Figure 45.

# POWER DISSIPATION/AMPLIFIER vs OUTPUT POWER





#### **APPLICATION INFORMATION**

#### GAIN SETTING RESISTORS, R<sub>F</sub> and R<sub>I</sub>

The gain for the TPA122 is set by resistors  $R_F$  and  $R_I$  according to Equation 1.

$$Gain = -\left(\frac{R_F}{R_I}\right) \tag{1}$$

Given that the TPA122 is an MOS amplifier, the input impedance is high. Consequently, input leakage currents are not generally a concern, although noise in the circuit increases as the value of  $R_F$  increases. In addition, a certain range of  $R_F$  values is required for proper start-up operation of the amplifier. Taken together, it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 k $\Omega$  and 20 k $\Omega$ . The effective impedance is calculated in Equation 2.

Effective Impedance = 
$$\frac{R_F R_I}{R_F + R_I}$$
 (2)

As an example, consider an input resistance of 20 k $\Omega$  and a feedback resistor of 20 k $\Omega$ . The gain of the amplifier would be -1 and the effective impedance at the inverting terminal would be 10 k $\Omega$ , which is within the recommended range.

For high-performance applications, metal film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of  $R_F$  above 50  $k\Omega$ , the amplifier tends to become unstable due to a pole formed from  $R_F$  and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor of approximately 5 pF should be placed in parallel with  $R_F$ . In effect, this creates a low-pass filter network with the cutoff frequency defined in Equation 3.

$$f_{c(lowpass)} = \frac{1}{2\pi R_F C_F}$$
 (3)

For example, if  $R_F$  is 100 k $\Omega$  and  $C_F$  is 5 pF, then  $f_{c(lowpass)}$  is 318 kHz, which is well outside the audio range.

#### INPUT CAPACITOR C

In the typical application, an input capacitor,  $C_I$ , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case,  $C_I$  and  $R_I$  form a high-pass filter with the corner frequency determined in Equation 4.

$$f_{c(highpass)} = \frac{1}{2\pi R_{I}C_{I}}$$
 (4)

The value of  $C_l$  is important to consider, as it directly affects the bass (low-frequency) performance of the circuit. Consider the example where  $R_l$  is 20 k $\Omega$  and the specification calls for a flat bass response down to 20 Hz. Equation 4 is reconfigured as Equation 5.

$$C_{I} = \frac{1}{2\pi R_{I} f_{c(highpass)}}$$
 (5)

In this example,  $C_l$  is 0.4  $\mu F$ , so one would likely choose a value in the range of 0.47  $\mu F$  to 1  $\mu F$ . A further consideration for this capacitor is the leakage path from the input source through the input network  $(R_l, C_l)$  and the feedback resistor  $(R_F)$  to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high-gain applications (> 10). For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications, as the dc level there is held at  $V_{DD}/2$ , which is likely higher than the source dc level. Note that it is important to confirm the capacitor polarity in the application.



#### **APPLICATION INFORMATION (continued)**

#### POWER SUPPLY DECOUPLING, Cs

The TPA122 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure that the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1  $\mu$ F, placed as close as possible to the device  $V_{DD}$  lead, works best. For filtering lower frequency noise signals, a larger aluminum electrolytic capacitor of 10  $\mu$ F or greater placed near the power amplifier is recommended.

#### MIDRAIL BYPASS CAPACITOR, CR

The midrail bypass capacitor,  $C_B$ , serves several important functions. During start-up,  $C_B$  determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it can not be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 160-k $\Omega$  source inside the amplifier. To keep the start-up pop as low as possible, the relationship shown in Equation 6 should be maintained.

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}} \times 160 \,\mathsf{k}\Omega\right)} \le \frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \tag{6}$$

As an example, consider a circuit where  $C_B$  is 1  $\mu F$ ,  $C_I$  is 1  $\mu F$ , and  $R_I$  is 20  $k\Omega$ . Inserting these values into Equation 6 results in:  $6.25 \le 50$  which satisfies the rule. Bypass capacitor,  $C_B$ , values of 0.1- $\mu F$  to 1- $\mu F$  ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.

#### **OUTPUT COUPLING CAPACITOR, Cc**

In the typical single-supply, single-ended (SE) configuration, an output coupling capacitor ( $C_{\rm C}$ ) is required to block the dc bias at the output of the amplifier, thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by Equation 7.

$$f_{C} = \frac{1}{2\pi R_{L} C_{C}} \tag{7}$$

The main disadvantage, from a performance standpoint, is that the typically small load impedances drive the low-frequency corner higher. Large values of  $C_C$  are required to pass low frequencies into the load. Consider the example where a  $C_C$  of 68  $\mu$ F is chosen and loads vary from 32  $\Omega$  to 47  $k\Omega$ . Table 1 summarizes the frequency response characteristics of each configuration.

Table 1. Common Load Impedances vs Low Frequency Output Characteristics in SE Mode

R <sub>L</sub>	c <sub>c</sub>	LOWEST FREQUENCY
32 Ω	68 μF	73 Hz
10,000 Ω	68 μF	0.23 Hz
47,000 Ω	68 μF	0.05 Hz

As Table 1 indicates, headphone response is adequate and drive into line level inputs (a home stereo for example) is good.

The output coupling capacitor required in single-supply, SE mode also places additional constraints on the selection of other components in the amplifier circuit. With the rules described earlier still valid, add the following relationship:



$$\frac{1}{\left(C_{\mathsf{B}} \times 160 \,\mathrm{k}\Omega\right)} \le \frac{1}{\left(C_{\mathsf{I}} \mathsf{R}_{\mathsf{I}}\right)} \ll \frac{1}{\mathsf{R}_{\mathsf{L}} C_{\mathsf{C}}} \tag{8}$$

#### **USING LOW-ESR CAPACITORS**

Low-ESR capacitors are recommended throughout this application. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

#### **5-V VERSUS 3.3-V OPERATION**

The TPA122 was designed for operation over a supply range of 2.5 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation because these are considered to be the two most common standard voltages. There are no special considerations for 3.3-V versus 5-V operation as far as supply bypassing, gain setting, or stability. The most important consideration is that of output power. Each amplifier in the TPA122 can produce a maximum voltage swing of  $V_{DD}-1$  V. This means, for 3.3-V operation, clipping starts to occur when  $V_{O(PP)}=2.3$  V, as opposed to  $V_{O(PP)}=4$  V for 5-V operation. The reduced voltage swing subsequently reduces maximum output power into the load before distortion begins to become significant.





i.com 18-Apr-2006

#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp (3)
TPA122D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DGN	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DGNG4	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DGNRG4	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA122EVM	OBSOLETE			0		TBD	Call TI	Call TI

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 17-Apr-2009

### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA122DGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TPA122DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 17-Apr-2009



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA122DGNR	MSOP-PowerPAD	DGN	8	2500	358.0	335.0	35.0
TPA122DR	SOIC	D	8	2500	346.0	346.0	29.0

DGN (S-PDSO-G8)

### PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-187 variation AA-T

#### PowerPAD is a trademark of Texas Instruments.



## DGN (S-PDSO-G8)

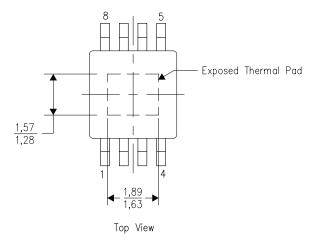
## PowerPAD™ PLASTIC SMALL OUTLINE

#### THERMAL INFORMATION

This PowerPAD  $^{\text{M}}$  package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

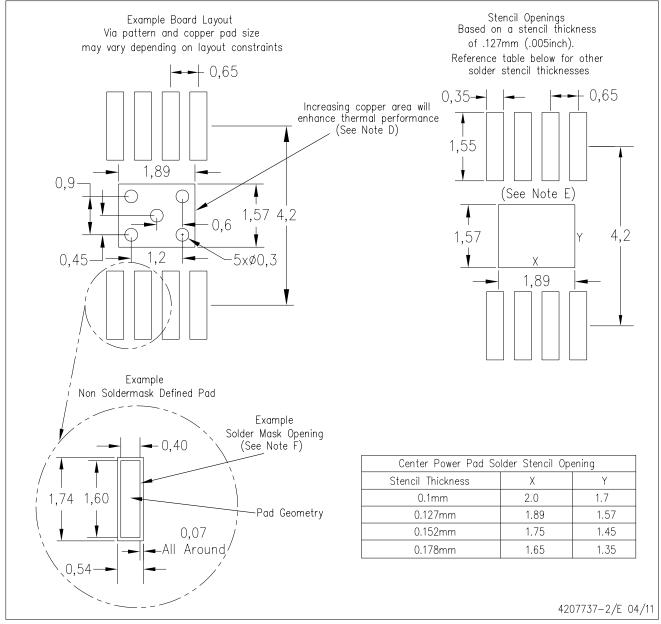
4206323-2/H 05/11

NOTE: All linear dimensions are in millimeters



## DGN (R-PDSO-G8)

### PowerPADTM PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

#### PowerPAD is a trademark of Texas Instruments



### D (R-PDSO-G8)

#### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



## D (R-PDSO-G8)

### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Audio	www.ti.com/audio	Communications and Telecom	www.ti.com/communications
Amplifiers	amplifier.ti.com	Computers and Peripherals	www.ti.com/computers
Data Converters	dataconverter.ti.com	Consumer Electronics	www.ti.com/consumer-apps
DLP® Products	www.dlp.com	Energy and Lighting	www.ti.com/energy
DSP	dsp.ti.com	Industrial	www.ti.com/industrial
Clocks and Timers	www.ti.com/clocks	Medical	www.ti.com/medical
Interface	interface.ti.com	Security	www.ti.com/security
Logic	logic.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Power Mgmt	power.ti.com	Transportation and Automotive	www.ti.com/automotive
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com	Wireless	www.ti.com/wireless-apps
RF/IF and ZigBee® Solutions	www.ti.com/lprf		

**TI E2E Community Home Page** 

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2011, Texas Instruments Incorporated

e2e.ti.com